

# DPG30C200PC

## **HiPerFRED**

 $V_{RRM} = 200 V$ 

 $I_{FAV} = 2x \quad 15 A$ 

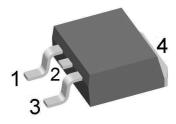
 $t_{rr} = 35 \, \text{ns}$ 

High Performance Fast Recovery Diode Low Loss and Soft Recovery Common Cathode

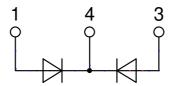
Part number

#### DPG30C200PC

Marking on Product: DPG30C200PC



Backside: cathode



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

#### **Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

#### **Disclaimer Notice**

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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse blockii	ng voltage	$T_{VJ} = 25^{\circ}C$			200	V
V <sub>RRM</sub>	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			200	V
I <sub>R</sub>	reverse current, drain current	V <sub>R</sub> = 200 V	$T_{VJ} = 25^{\circ}C$			1	μΑ
		$V_R = 200 V$	$T_{VJ} = 150$ °C			0.08	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 15 A	$T_{VJ} = 25^{\circ}C$			1.26	٧
		$I_F = 30 A$				1.51	٧
		I <sub>F</sub> = 15 A	T <sub>VJ</sub> = 150°C			1.01	٧
		$I_F = 30 A$				1.29	٧
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 145°C	T <sub>vJ</sub> = 175°C			15	Α
		rectangular d = 0.5					
V <sub>F0</sub>	threshold voltage		T <sub>VJ</sub> = 175°C			0.69	٧
r <sub>F</sub>	slope resistance	ss calculation only				18	mΩ
R <sub>thJC</sub>	thermal resistance junction to case	;				1.7	K/W
R <sub>thCH</sub>	thermal resistance case to heatsin	k			0.25		K/W
P <sub>tot</sub>	total power dissipation		$T_{C} = 25^{\circ}C$			90	W
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			240	Α
C¹	junction capacitance	$V_R = 150  \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		20		pF
I <sub>RM</sub>	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		3		Α
		$I_F = 15 \text{ A}; V_R = 130 \text{ V}$	$T_{VJ} = 125$ °C		6.5		Α
t <sub>rr</sub>	reverse recovery time	$\begin{cases} I_F = 15 \text{ A}; V_R = 130 \text{ V} \\ -\text{di}_F/\text{dt} = 130 \text{ A}/\mu\text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		35		ns
	)		$T_{VJ} = 125$ °C		55		ns





Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal			35	Α
T <sub>VJ</sub>	virtual junction temperature		-55	5	175	°C
T <sub>op</sub>	operation temperature		-55	5	150	°C
T <sub>stg</sub>	storage temperature		-55	5	150	°C
Weight				1.5		g
F <sub>c</sub>	mounting force with clip		20	)	60	N

# **Product Marking XXXXXXXXX** Part Number IXYS yywwZ Logo Date Code Location **→**123456 Lot#

#### Part description

D = Diode

P = HiPerFRED

G = extreme fast

30 = Current Rating [A]

C = Common Cathode

200 = Reverse Voltage [V] PC = TO-263AB (D2Pak) (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG30C200PC-TRL	DPG30C200PC	Tape & Reel	800	506675
Alternative	DPG30C200PC-TUB	DPG30C200PC	Tube	50	525099

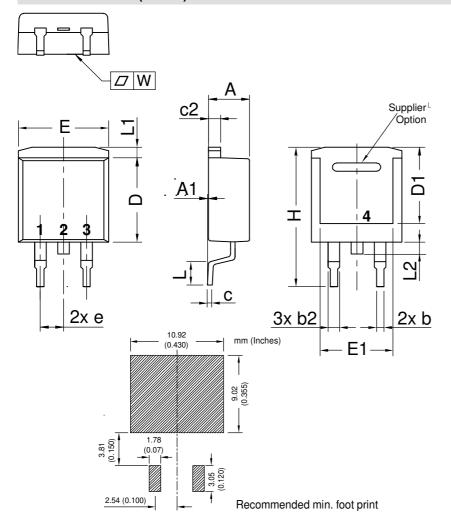
Similar Part	Package	Voltage class
DPG30C200PB	TO-220AB (3)	200
DPG30C200HB	TO-247AD (3)	200

<b>Equivalent Circuits for Simulation</b>			* on die level	$T_{VJ} = 175^{\circ}C$
$I \rightarrow V_0$	$R_0$	Fast Diode		
V <sub>0 max</sub>	threshold voltage	0.69		V
$R_{0 \text{ max}}$	slope resistance *	14.7		$m\Omega$





### Outlines TO-263 (D2Pak)



Dim.	Millir	neter	Inc	hes	
DIIII.	min	max	min	max	
Α	4.06	4.83	0.160	0.190	
A1	typ.	0.10	typ. C	.004	
A2	2.	41	0.095		
b	0.51	0.99	0.020	0.039	
b2	1.14	1.40	0.045	0.055	
С	0.40	0.74	0.016	0.029	
c2	1.14	1.40	0.045	0.055	
D	8.38	9.40	0.330	0.370	
D1	8.00	8.89	0.315	0.350	
D2	2	.5	0.098		
Е	9.65	10.41	0.380	0.410	
E1	6.22	8.50	0.245	0.335	
е	2,54 BSC		0,100 BSC		
e1	4.28		0.169		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	1.02	1.68	0.040	0.066	
W	typ. 0.02	0.040	typ. 0.0008	0.002	

All dimensions conform with and/or within JEDEC standard.

